

TO-92 Plastic-Encapsulate Transistors

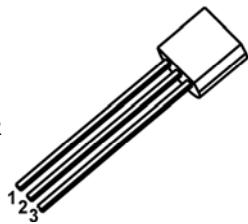
KTC3194 TRANSISTOR (NPN)

FEATURES

- General Purpose Switching Application

TO - 92

- 1.EMITTER
- 2.COLLECTOR
- 3.BASE



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	0.02	A
P_c	Collector Power Dissipation	0.625	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = 1\text{mA}, I_B = 0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}, I_C = 0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			0.5	μA
DC current gain	h_{FE}	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	40		200	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 15\text{mA}, I_B = 1.5\text{mA}$			0.2	V
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$		550		MHz

CLASSIFICATION OF h_{FE}

RANK	R	O	Y
RANGE	40-80	70-140	100-200